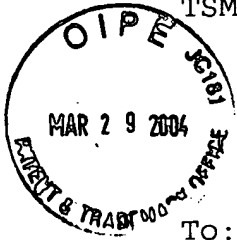


TSMC-01-1582D



March 19, 2004

To: Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Fr: George O. Saile, Reg. No. 19,572
28 Davis Avenue
Poughkeepsie, N.Y. 12603

Subject:

Serial No. 10/781,182 02/18/04

Chang-Ming Dai et al.

FULL SIZED SCATTERING BAR ALT-PSM
TECHNIQUE FOR IC MANUFACTURING IN
SUB-RESOLUTION ERA

INFORMATION DISCLOSURE STATEMENT

Enclosed is Form PTO-1449, Information Disclosure Citation
In An Application.

The following Patents and/or Publications are submitted to
comply with the duty of disclosure under CFR 1.97-1.99 and
37 CFR 1.56.

CERTIFICATE OF MAILING

I hereby certify that this correspondence is being
deposited with the United States Postal Service as first class
mail in an envelope addressed to: Commissioner for Patents,
P.O. Box 1450, Alexandria, VA 22313-1450, on March 25, 2004.

Stephen B. Ackerman, Reg.# 37761

Signature/Date

Stephen B. Ackerman 3/25/04

U.S. Patent 6,210,841 to Lin et al., "Approach to Increase the Resolution of Dense Line/Space Patterns for 0.18 Micron and Below Design Rules Using Attenuating Phase Shifting Masks," discusses forming an attenuated mask by adding an attenuator material such as MoSiOxNy to portions of the substrate.

The following two U.S. Patents reveal double exposure alt-phase shift mask (PSM) methods:

- 1) U.S. Patent 6,228,539 to Wang et al., "Phase Shifting Circuit Manufacture Method and Apparatus."
- 2) U.S. Patent 5,573,890 to Spence, "Method of Optical Lithography Using Phase Shift Masking."

U.S. Patent 5,858,580 to Wang et al., "Phase Shifting Circuit Manufacture Method and Apparatus," discloses a phase shift mask (PSM) process.

U.S. Patent 5,994,002 to Matsuoka, "Photo Mask and Pattern Forming Method," describes a alt-PSM technique.

U.S. Patent 5,882,827 to Nakao, "Phase Shift Mask, Method of Manufacturing Phase Shift Mask and Method of Forming a Pattern Using Phase Shift Mask," describes a phase shift mask (PSM) method.

Sincerely,



Stephen B. Ackerman, Reg.# 37761

Form PTO-1449

Sheet 1 of 1

**INFORMATION DISCLOSURE CITATION
IN AN APPLICATION**

MAR 29 2004

(Use several sheets if necessary)

Document Number (Optional)

TSMC-01-1582D

Application Number

10/781,182

Applicant

Chang-Ming Dai et al.

Filing Date

02/18/04

Drawn At Unit

U. S. PATENT DOCUMENTS

EXAMINER INITIAL	DOCUMENT NUMBER	DATE	TITLE	CLASS	SUBCLASS	NUMERO DATE X APPROPRIATE
	6210841	4/3/01	Lin et al.	430	5	9/7/99
	6228539	5/8/01	Wang et al.	430	5	1/12/99
	5573890	11/12/96	Spence	430	311	7/18/94
	5858580	1/12/99	Wang et al.	430	5	9/17/97
	5994002	11/30/99	Matsuoka	430	5	9/4/97
	5882827	3/16/99	Nakao	430	5	1/27/97

FOREIGN PATENT DOCUMENTS

	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	Translation	
						YES	NO

OTHER DOCUMENTS (Including Author, Title, Date, Portion of Pages, Etc.)

EXAMINER

DATE CONSIDERED

EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP § 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to the applicant.